In the claims:

1. (Previously presented) A method of structuring of a substrate comprising the steps of:

providing a polymerization starter layer on the substrate comprising a plurality of polymerization starters, wherein the polymerization starter layer comprises azomonochlorsilane,

applying a radiation field to the polymerization starter layer for selectively reducing a density of polymerization starters of the polymerization starter layer,

applying monomers to the polymerization starter layer,

polymerizing the monomers, the polymerizing being initiated by the starters of the polymerization starter layer, and

structuring the substrate using the polymerized monomers as a mask.

2. (Original) The method of claim 1 further comprising immobilizing the polymerization starters on a surface of the substrate.

3. (Previously presented) The method of claim 1further comprising providing a coating directly on the substrate for forming of covalent bonds with the polymerization starters.

4. (Original) The method of claim 3, wherein the coating contains SiOx.

5. (Original) The method of claim 1, wherein the radiation field is a UV radiation field.

6. (Original) The method of claim 1, wherein the density of the polymerization starters is selectively reduced by cracking of some of the polymerization starters.

7. (Original) The method of claim1, wherein the polymerization starter layer being a mono-molecular layer of polymerization starters.

8. (Original) The method of claim 1, wherein the radiation field is provided by means of a radiation source and a gray or a grating mask.

9. (Original) The method of claim 1, wherein the radiation field is chosen to provide a lens structure in the substrate, the lens structure having a defined focalpoint

10. (Original) The method claim 1 comprising performing a semi-conductor manufacturing step using the polymerized monomers as a mask.

11. (Original) The method of claim 1,wherein the step of structuring the substrate being performed by an ion mill, reactive ion etch (RIE) or wet etch process.

12. (Original) The method of claim 1 wherein in the step of polymerizing the monomers, a varied topography of the substrate is formed corresponding to the density of the polymerization starters of the polymerization starter layer, and

wherein in the step of structuring the substrate, the varied topography is reproduced into the substrate.

Claims 13 to 15 (Canceled).

16. (New) A method of structuring of a substrate comprising the steps of:

providing a polymerization starter layer on the substrate comprising a plurality of polymerization starters, wherein the polymerization starter layer comprises azomonochlorsilane,

applying a radiation source through a mask to the polymerization starter layer for selectively reducing a density of polymerization starters of the polymerization starter layer so that the density of the polymerization starters varies across the substrate,

applying monomers to the selectively reduced polymerization starter layer,

polymerizing the monomers, the polymerizing being initiated by the selectively reduced starters of the polymerization starter layer, and

etching the substrate using the polymerized monomers as a mask to pattern the substrate.

17. (New) The method of claim 16 wherein in the step of polymerizing the monomers, a varied topography of the substrate is formed corresponding to the density of the polymerization starters of the polymerization starter layer.

18. (New) The method of claim 1, wherein the radiation field is provided by means of a radiation source and a gray or a grating mask and wherein the radiation source is modulated by the gray or grating mask.